

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((soi or silicon adj on adj insulat\$4) and (ion adj implantation or ion adj implant\$4) near5 (hydrogen or "h.sub.2") and dry\$4 near5 (low adj pressure or vacuum)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 06:52
L2	0	((soi or silicon adj on adj insulat\$4) and (ion adj implantation or ion adj implant\$4) near5 (hydrogen or "h.sub.2") and dry\$4 with (low adj pressure or vacuum)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 06:52
L3	0	((soi or silicon adj on adj insulat\$4) and (ion adj implantation or ion adj implant\$4) near5 (hydrogen or "h.sub.2") and dry\$4 same (low adj pressure or vacuum)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 06:52
L4	0	((soi or silicon adj on adj insulat\$4) and (hydrogen or "h.sub.2") adj ion adj implantation and dry\$4 with (low adj pressure or vacuum)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 06:53
L5	0	((soi or silicon adj on adj insulat\$4) and (hydrogen or "h.sub.2") adj ion adj implant\$4 and dry\$4 with (low adj pressure or vacuum)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 06:53
L6	0	((soi or silicon adj on adj insulat\$4) and (hydrogen or "h.sub.2") adj (implantation or implant\$4) and dry\$4 with (low adj pressure or vacuum)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 06:54
L7	0	((soi or silicon adj on adj insulat\$4) and (hydrogen or "h.sub.2") with (dop\$3 or implantation or implant\$4) and dry\$4 with (low adj pressure or vacuum)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 06:54
L8	0	((soi or silicon adj on adj insulat\$4) and (hydrogen or "h.sub.2") with (dop\$3 or implantation or implant\$4) and dry\$4 same (low adj pressure or vacuum)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 06:54

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L9	8	((soi or silicon adj on adj insulat\$4) and (hydrogen or "h.sub.2") with (dop\$3 or implantation or implant\$4) and (low adj pressure or vacuum)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 06:55
L10	0	((soi or silicon adj on adj insulat\$4) and (hydrogen or "h.sub.2") with (dop\$3 or implantation or implant\$4) and (low adj pressure or vacuum) and rins\$3).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 06:55
S1	3	((("6323109") or ("6306730") or ("5374564")).PN.	USPAT	OR	OFF	2007/01/12 06:50
S2	835	(hydrogen or "h.sub.2") adj (implantation or ion adj implantation ion adj implanting or implanting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:53
S3	1231950	vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 08:26
S4	243	S2 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 08:28
S5	844	smart adj cut or smartcut	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 08:28
S6	60	S4 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 10:44
S7	720	ion adj (cut or cutting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 08:36

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S8	85	S7 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 08:36
S9	3495856	substrate or die or wafer or chip	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 08:36
S10	40	S8 and S9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 08:42
S11	1	09/505283.app.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 08:43
S12	3	"20030211705"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 08:43
S13	2996	anodic adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:18
S14	292	S3 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:18
S15	21	S13 and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:28
S16	412	vacuum adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:28

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S17	7	S5 and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:31
S18	6	low adj vacuum adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:32
S19	13	vacuum adj bonding near4 low	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:37
S20	50	vacuum adj bonding same low	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:32
S21	4	(dry or drying) near10 low adj vacuum and (bond or bonding) near4 (substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:44
S22	1439	(substrate or wafer) adj bonding and (cmp or chemical adj mechanical adj polishing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:47
S23	87	bond\$4 with low adj vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 11:34
S24	8	S22 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:46
S25	4078	(substrate or wafer) adj bonding and (cmp or chemical adj mechanical adj polishing or polishing or polish or clean)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 09:49

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S26	16	S23 and S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 11:27
S27	321278	low adj pressure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 11:27
S28	180	S27 and (S5 or S7)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 11:31
S29	756782	(split or splitting or cleave or cleaving or cleaved delaminate or delaminated or delamination)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:13
S30	74	S16 and S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 11:34
S31	313	bond\$4 with low near4 vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 11:35
S32	42	S29 and S31	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 11:35
S33	649	(split or splitting or cleave or cleaving or cleaved delaminate or delaminated or delamination or splice or splicing or spliced) and (hydrogen or "h.sub.2") adj (implant\$6 or ion adj implant\$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:15
S34	2655	low adj pressure adj vacuum\$3 or low near4 vaccum\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:16

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S35	0	S33 and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:16
S36	1231950	vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:17
S37	246	S33 and S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:31
S38	327245	low adj vacuum or low adj pressure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:32
S39	343872	low adj vacuum or low adj pressure or low near4 vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:36
S40	649	(split or splitting or cleave or cleaving or cleaved delaminate or delaminated or delamination or splice or splicing or spliced) and (hydrogen or "h.sub.2") adj (implant\$6 or ion adj implant\$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 14:00
S41	111	S40 and S39	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:32
S42	35229	low adj vacuum or low near4 vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:36
S43	18	S40 and S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:40

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S44	9	annealing near4 low adj vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:45
S45	4	(smart adj cut or smartcut) and annealing and low adj vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:46
S46	17	(anneal\$4) near4 low adj vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:46
S47	5	(smart adj cut or smartcut) and anneal\$4 and low adj vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:47
S48	4	(ion adj cut\$4) and anneal\$4 and low adj vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:52
S49	268	anneal\$4 near7 low adj pressure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 14:17
S50	0	S40 and S49	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:53
S51	835	(hydrogen or "h.sub.2") adj (implantation or ion adj implantation ion adj implanting or implanting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:53
S52	0	S51 and S49	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:54

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S53	3919	simox or separation adj by adj implant\$4 adj oxygen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 14:08
S54	9	S49 and S53	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 14:01
S55	33	ion adj implant\$4 and S49	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 14:08
S56	174	anneal\$4 near7 low near5 vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 14:17
S57	23	S49 and S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 14:18
S58	0	S51 and S57	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 14:18
S59	0	S51 and S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 14:18
S60	127	sacrificial adj layer and thermally adj grow\$3 adj silicon adj dioxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/15 17:27
S61	31	sacrificial adj layer and thermally adj grow\$3 adj silicon adj dioxide and remov\$3 near4 silicon adj dioxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/15 17:27

EAST Search History

S62	27	sacrificial adj layer and thermal near4 silicon adj dioxide and remov\$3 near4 silicon adj dioxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/15 17:27
S63	11	sacrificial adj layer and eklund.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/15 17:48
S64	1	09/857803.app.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/15 17:49
S65	25	("20020127820" "20040063298" "5494849" "5668045" "5834812" "5863832" "5937312" "5989981" "6074479" "6103599" "6140210" "6191007" "6224668" "6238990" "6245645" "6251754" "6261362" "6284628" "6284629" "6312797" "6313014" "6350703" "6387829" "6403502" "6613678").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/06/15 17:52
S66	0	(substrate or wafer) adj clean\$3 and dry\$3 near low adj vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/15 17:53
S67	75812	soi or silicon adj on adj insulat\$4 or silicon-on-insulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 09:55
S68	1278373	vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 09:55
S69	823913	split\$4 or splic\$4 or exfoliat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 09:55

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S70	1253	S67 and S68 and S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 09:56
S71	1838366	dry\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 09:56
S72	526	S70 and S71	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 09:58
S73	360	semiconductor and S72	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 09:59
S74	301	smart adj cut and vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 10:10
S75	29949	hydrophobic near3 surface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 10:10
S76	11	S74 and S75	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 10:10
S77	19	("4963505" "5354695" "5783477" "5877070" "5915167" "6120917" "6143628" "6153445" "6198159" "6246068" "6255731").PN. OR ("6563133"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/11 10:59
S78	7	S71 and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 11:41

EAST Search History

S79	2	"7019339".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 11:42
S80	90	(spin-dry\$3 or spin adj dry\$3) near5 (vacuum or low adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:51
S81	856	smart adj cut	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 11:43
S82	0	S80 and S81	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 11:43
S83	1389	438/455.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 11:46
S84	0	S80 and S83	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 11:46
S85	77310	(dry\$3) near5 (vacuum or low adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 11:57
S86	15	S83 and S85	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 11:51
S87	104549	(dry\$3) with (vacuum or low adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:15

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S88	22	S83 and S87	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 11:57
S89	7	S88 not S86	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:00
S90	980	438/458.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:07
S91	13	(S85 or S87) and S90	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:01
S92	298	438/456.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:02
S93	1056	438/459.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:02
S94	683	257/e21.122.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:07
S95	199236	(dry\$3) same (vacuum or low adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:23
S96	67	S83 and S95	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:15

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S97	420754	(dry\$3) and (vacuum or low adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:23
S98	246	S83 and S97	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:39
S99	2645	(ion adj implantation or ion adj implant\$4) with (hydrogen or "h. sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:40
S10 0	469	(S87 or S85 or S95 or S97) and S99	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:41
S10 1	76	(S83 or S90 or S92 or S93) and S100	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 12:41
S10 2	154	(spin-dry\$3 or spin adj dry\$3) with (vacuum or low adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 13:23
S10 3	24264	bond\$3 with (low adj pressure or vacuum or vaccum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 13:24
S10 4	178	S83 and S103	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 13:24
S10 5	21	("4998665").URPN.	USPAT	OR	ON	2007/01/11 13:25
S10 6	8	("6563133").URPN.	USPAT	OR	ON	2007/01/11 13:36

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S10 7	30	S99 and S104	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 13:57
S10 8	1232	438/514.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 13:57
S10 9	205	438/515.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 13:57
S11 0	60	S97 and S108	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 13:59
S11 1	13	S97 and S109	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 13:58
S11 2	257	257/e21.12.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 14:09
S11 3	455	257/e21.121.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 14:12
S11 4	683	257/e21.122.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 14:12
S11 5	279	257/e21.123.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 14:12

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S11 6	37	257/e21.124.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 14:13
S11 7	669	257/e21.567.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 14:13
S11 8	805	257/e21.568.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 14:14
S11 9	215	257/e21.569.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 14:13
S12 0	316	257/e21.57.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 15:27

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2580	((delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4 or cut\$4 or exfoilat\$4) with (hydrogen or "h.sub.2") and semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:40
L2	1393	438/455.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:32
L3	300	438/456.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:32
L4	113	438/457.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:32
L5	984	438/458.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:32
L6	212	(2 or 3 or 4 or 5) and 1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:35
L7	202632	(delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4 or cut\$4 or exfoilat\$4) with pressure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:35
L8	119	(2 or 3 or 4 or 5) and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:35

EAST Search History

L9	509	(delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4 or cut\$4 or exfoilat\$4) with ((ion adj implant\$4 or implantation) with (hydrogen or "h.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 14:06
L10	1776802	semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:43
L11	442	9 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:43
L12	9523	anneal\$4 with (low adj pressure or vacuum or reduced adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:50
L13	10	9 and 12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:49
L15	15232	(heat adj treat\$4) with (low adj pressure or vacuum or reduced adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:51
L16	5	9 and 15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 13:51
L17	0	(11/348502).APP.	USPAT; USOCR	OR	ON	2007/01/22 13:53
L19	275	(atmosphere or atm or pascal or Pa or megapascal or kilopascal or bar or mbar or millibar or mm adj hg or millitorr or torr) and 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 14:00

EAST Search History

L20	515	(delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4 or cut\$4 or exfoilat\$4) with ((ion adj implant\$4 or implantation) same (hydrogen or "h.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 14:06
L22	724	(delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4 or cut\$4 or exfoilat\$4) same ((ion adj implant\$4 or implantation) with (hydrogen or "h.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 14:07

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"6274459".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:13
L2	2	"6286524".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:06
L3	1	"6274459".pn. and vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:25
L4	0	"6274459".pn. and low adj pressure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:21
L5	860	smart adj cut or "smart cut"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:25
L6	1535234	vacuum or low adj pressure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:25
L7	0	5 with 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:26
L8	0	smart adj cut with (vacuum or low adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:27

EAST Search History

L9	0	smart adj cut with (vacuum or low adj pressure or reduced adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:27
L10	0	smart adj cut with (vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:27
L11	3	smart adj cut same (vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:28
L12	0	smart adj cut same (vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:28
L13	3	smart adj cut same (vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:29
L14	95646	cut same (vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:30
L15	28907	cut with (vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:30
L16	4	ion adj cut with (vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:30
L17	0	smart near2 cut with (vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:30

EAST Search History

L18	3	smart near2 cut same (vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:07
L19	574	438/455.ccls. and (vacuum or low adj pressur\$4 or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:33
L20	399	438/458.ccls. and (vacuum or low adj pressur\$4 or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:33
L21	11	("20020190269" "5603779" "5769991" "5882987").PN. OR ("6645831").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/22 11:52
L22	1749909	(vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:50
L23	8	21 and 22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:50
L24	2238023	(vacuum or low with pressure or reduc\$4 with pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:51
L26	1393	438/455.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:51
L28	984	438/458.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:51

EAST Search History

L29	604	24 and 26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:51
L30	428	24 and 28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:51
L31	0	"5882987".pn. and 24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:52
L32	415	(delamin\$4 or delamination) with (vacuum or low adj pressure or reduc\$4 adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:08
L33	74	(delamin\$4 or delamination) with (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:12
L34	753	((delamin\$4 or delamination or splic\$4 or split\$4 or remov\$3) with (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:22
L35	23487	((delamin\$4 or delamination or splic\$4 or split\$4 or remov\$3) with (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:14
L36	6	(19 or 20) and 34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:15
L37	98	(19 or 20) and 35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:15

EAST Search History

L38	13	((delamin\$4 or delamination or splic\$4 or split\$4) with (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:23
L39	25	((delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4) with (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:24
L40	260	257/e21.12.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:24
L41	787	((delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4) with (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:27
L42	23927	((delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4) and (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:29
L43	6	40 and 42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:26
L44	147	438/for.104.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:26
L45	0	40 and 44	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:26
L46	0	42 and 44	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:26

EAST Search History

L47	682	257/e21.567.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:31
L48	62	42 and 47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:27
L49	2	41 and 47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:27
L50	23927	((delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4 or exfoilat\$4) and (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:30
L51	61571	((delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4 or exfoilat\$4 or cut\$4) and (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:30
L52	3253	((delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4 or exfoilat\$4 or cut\$4) with (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:32
L53	34	(26 or 28) and 52	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:31
L54	3	47 and 52	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:32
L55	74	((delamin\$4 or delamination or splic\$4 or split\$4 or cleav\$4 or exfoilat\$4 or cut\$4) with (vacuum or low adj pressure or reduc\$4 adj pressure) and semiconductor).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:32